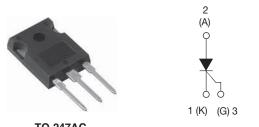
**Vishay Semiconductors** 

# Thyristor High Voltage, Phase Control SCR, 40 A



www.vishay.com

**TO-247AC** 

PRODUCT SUMMARY							
Package	TO-247AC						
Diode variation	Single SCR						
I <sub>T(AV)</sub>	35 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V						
V <sub>TM</sub>	1.45 V						
I <sub>GT</sub>	150 mA						
TJ	-40 °C to +125 °C						

## **FEATURES**

- Designed and gualified according to JEDEC<sup>®</sup>-JESD 47
- Low I<sub>GT</sub> parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

## DESCRIPTION

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	35	Α					
I <sub>RMS</sub>		55	~					
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V					
I <sub>TSM</sub>		600	A					
V <sub>T</sub>	40 A, T <sub>J</sub> = 25 °C	1.45	V					
dV/dt		1000	V/µs					
dl/dt		100	A/µs					
TJ		-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-40TPS08AP-S1	800	900	10						
VS-40TPS12AP-S1	1200	1300	10						

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# VS-40TPS...AP-S1 Series



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 79 \ ^{\circ}C$ , 180° conduction half sine wav	35			
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>		55	А		
Maximum peak, one-cycle	<b></b>	10 ms sine pulse, rated $V_{\text{RRM}}$ applied		500		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied		600		
Maximum 1 <sup>2</sup> t for fueing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	Initial $T_{1} = T_{1} max.$	1250	A <sup>2</sup> s	
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no voltage reapplied	- 1 <u>5</u> – 1 <u>5</u> max.	1760	A-S	
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	17 600	A²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>		1.02	v		
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 105 00	1.23			
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C	9.74			
High level value of on-state slope resistance	r <sub>t2</sub>		7.50	mΩ		
Maximum peak on-state voltage	V <sub>TM</sub>	110 A, T <sub>J</sub> = 25 °C		1.85	V	
Maximum rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C	100	A/µs		
Maximum holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $T_J$	200			
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25$	300	1		
		$T_J = 25 \text{ °C}$	0.5	mA		
Maximum reverse and direct leakage current	I <sub>RRM/</sub> I <sub>DRM</sub>	$T_J = 125 \text{ °C}$ $V_R = \text{Rated } V_{RRM}/V_L$	PRM	10		
Maximum rate of rise of off-state voltage 40TPSAP-S1 Series	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$	- k = 100 Ω	500	V/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>			10	W
Maximum average gate power	P <sub>G(AV)</sub>			2.5	vv
Maximum peak gate current	I <sub>GM</sub>			2.5	А
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	V
		T <sub>J</sub> = - 40 °C		4.0	V
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	2.5	
		T <sub>J</sub> = 125 °C		1.7	
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		270	mA
M		T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	150	
Maximum required DC gate current to trigger		T <sub>J</sub> = 125 °C		80	
		$T_J = 25 \text{ °C}, \text{ for } 40 \text{TPS08AP}$	40		
Maximum DC gate voltage not to trigger for 40TPS12AP-S1	V <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		0.15	V
Maximum DC gate curr ent not to trigger for 40TPS12AP-S1	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated	1	mA	

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case	R <sub>thJC</sub>		0.6	-			
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>	DC operation	40	°C/W			
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2				
A navavimeta usiaht			6	g			
Approximate weight			0.21	oz.			
minir	num		6 (5)	kgf ⋅ cm			
Mounting torque maxir	num		12 (10)	(lbf · in)			
Marking daviaa		Case style TO-247AC	40TPS	08AP-S1			
Marking device		Case Sigle 10-247AC	40TPS	40TPS12AP-S1			

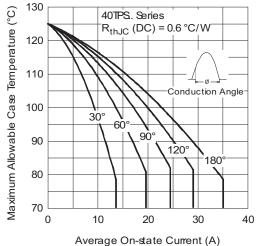
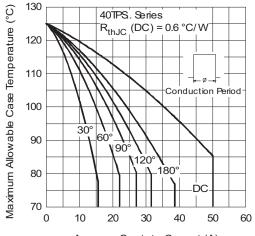
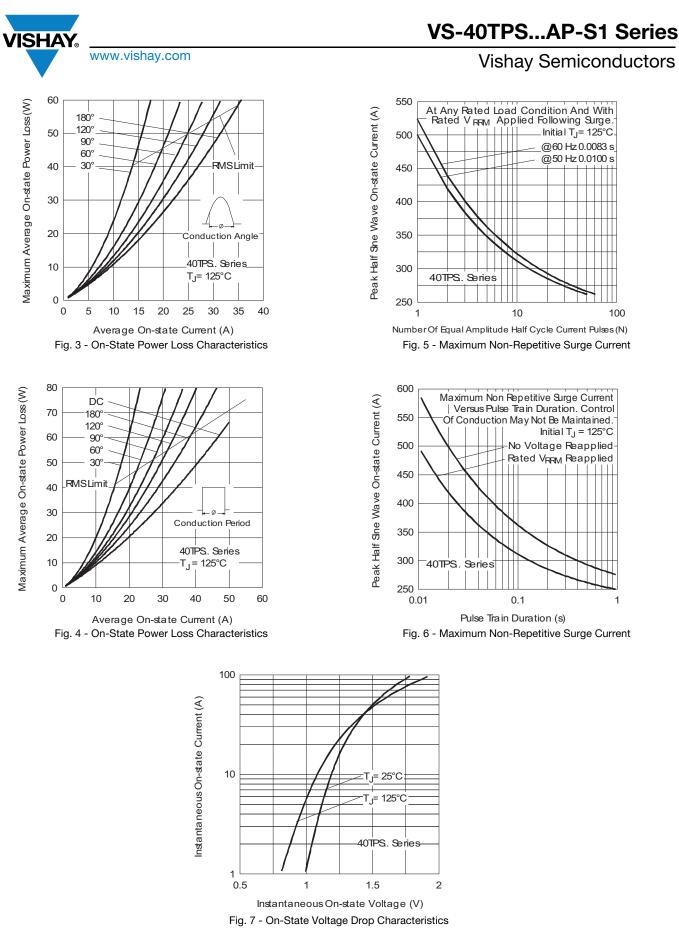


Fig. 1 - Current Rating Characteristics



Average On-state Current (A) Fig. 2 - Current Rating Characteristics





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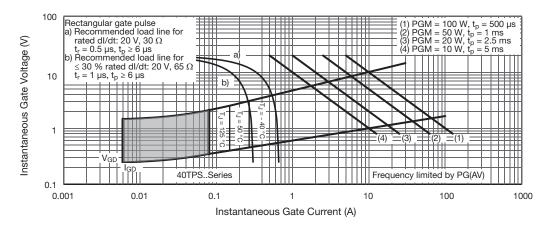


Fig. 8 - Gate Characteristics

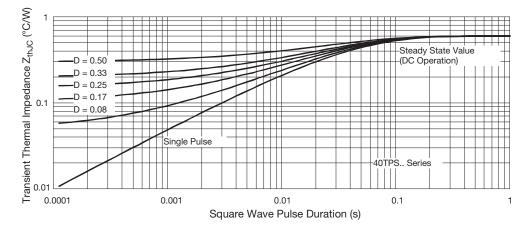


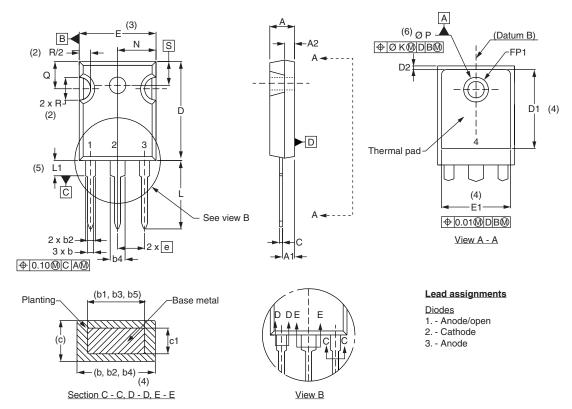
Fig. 9 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

# **Outline Dimensions**





## **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		HES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			e	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			FK	2.	54	0.0	)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			Ν	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ΦP	3.56	3.66	0.14	0.144	
с	0.38	0.86	0.015	0.034			Φ <b>P1</b>	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	1.78	0.216	
D1	13.08	_	0.515	-	4		S	5.51	BSC	0.217	BSC	

### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

<sup>(7)</sup> Outline conforms to JEDEC outline TO-247 with exception of dimension c

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